

Physics 211B : ssignment #2

[1] *Rectangular Barrier* – Consider a symmetric planar barrier consisting of a layer of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ of width $2a$ imbedded in GaAs. The barrier height V_0 is simply the difference between conduction band minima ΔE_c at the Γ point; energies are defined relative to E_{Γ}^{GaAs} . Derive the \mathcal{S} -matrix for this problem. Show that

$$T(E) = \frac{1}{1 + \left[\frac{\sinh(b\sqrt{1-\eta})}{2\sqrt{\eta(1-\eta)}} \right]^2} \quad (\eta \leq 1)$$

and

$$T(E) = \frac{1}{1 + \left[\frac{\sin(b\sqrt{\eta-1})}{2\sqrt{\eta(\eta-1)}} \right]^2} \quad (\eta \geq 1) ,$$

where $\eta = E/V_0$ and $b = a/\ell$ with $\ell = \hbar/\sqrt{2m^*V_0}$. Sketch $T(E)$ versus E/V_0 for various values of the dimensionless thickness b .

[2] *Multichannel Scattering* – Consider a multichannel scattering process defined by the Hamiltonian matrix

$$\mathcal{H}_{ij} = \left(-\frac{\hbar^2}{2m} \frac{\partial^2}{\partial x^2} + \varepsilon_i \right) \delta_{ij} + \Omega_{ij} \delta(x) ,$$

which describes the scattering among N channels by a δ -function impurity at $x = 0$. The matrix Ω_{ij} allows a particle in channel j passing through $x = 0$ to be scattered into channel i . The $\{\varepsilon_i\}$ are the internal (transverse) energies for the various channels. For $x \neq 0$, we can write the channel j component of the wavefunction as

$$\begin{aligned} \psi_j(x) &= I_j e^{ik_j x} + O'_j e^{-ik_j x} & (x < 0) \\ &= O_j e^{ik_j x} + I'_j e^{-ik_j x} & (x > 0) , \end{aligned}$$

where the k_j are positive and determined by

$$\varepsilon_j = \frac{\hbar^2 k_j^2}{2m} + \varepsilon_j .$$

Show that the incoming and outgoing flux amplitudes are related by a $2N \times 2N$ \mathcal{S} -matrix:

$$\begin{pmatrix} \sqrt{v} O' \\ \sqrt{v} O \end{pmatrix} = \overbrace{\begin{pmatrix} r & t' \\ t & r' \end{pmatrix}}^{\mathcal{S}} \begin{pmatrix} \sqrt{v} I \\ \sqrt{v} I' \end{pmatrix}$$

where $v = \text{diag}(v_1, \dots, v_N)$ with $v_i = \hbar k_i/m > 0$. Find explicit expressions for the component $N \times N$ blocks r, t, t', r' , and show that \mathcal{S} is unitary, *i.e.* $\mathcal{S}^\dagger \mathcal{S} = \mathcal{S} \mathcal{S}^\dagger = \mathbb{I}$.

[3] *Spin Valve* – Consider a barrier between two halves of a ferromagnetic metallic wire. For $x < 0$ the magnetization lies in the \hat{z} direction, while for $x > 0$ the magnetization is

directed along the unit vector $\hat{\mathbf{n}} = (\sin \theta \cos \phi, \sin \theta \sin \phi, \cos \theta)$. The Hamiltonian is given by

$$\mathcal{H} = -\frac{\hbar^2}{2m^*} \frac{d^2}{dx^2} + \mu_B \mathbf{H}_{\text{int}} \cdot \boldsymbol{\sigma} ,$$

where \mathbf{H}_{int} is the (spontaneously generated) internal magnetic field and $\mu_B = e\hbar/2m_e c$ is the Bohr magneton¹. The magnetization \mathbf{M} points along \mathbf{H}_{int} ². For $x < 0$ we therefore have

$$E_F = \frac{\hbar^2 k_{\uparrow}^2}{2m^*} + \Delta = \frac{\hbar^2 k_{\downarrow}^2}{2m^*} - \Delta ,$$

where $\Delta = \mu_B H_{\text{int}}$. A similar relation holds for the Fermi wavevectors corresponding to spin states $|\hat{\mathbf{n}}\rangle$ and $|-\hat{\mathbf{n}}\rangle$ in the region $x > 0$.

Consider the \mathcal{S} -matrix for this problem. The ‘in’ and ‘out’ states should be defined as local eigenstates, which means that they have different spin polarization axes for $x < 0$ and $x > 0$. Explicitly, for $x < 0$ we write

$$\begin{pmatrix} \psi_{\uparrow}(x) \\ \psi_{\downarrow}(x) \end{pmatrix} = \left\{ A_{\uparrow} e^{ik_{\uparrow}x} + B_{\uparrow} e^{-ik_{\uparrow}x} \right\} \begin{pmatrix} 1 \\ 0 \end{pmatrix} + \left\{ A_{\downarrow} e^{ik_{\downarrow}x} + B_{\downarrow} e^{-ik_{\downarrow}x} \right\} \begin{pmatrix} 0 \\ 1 \end{pmatrix} ,$$

while for $x > 0$ we write

$$\begin{pmatrix} \psi_{\uparrow}(x) \\ \psi_{\downarrow}(x) \end{pmatrix} = \left\{ C_{\uparrow} e^{ik_{\uparrow}x} + D_{\uparrow} e^{-ik_{\uparrow}x} \right\} \begin{pmatrix} u \\ v \end{pmatrix} + \left\{ C_{\downarrow} e^{ik_{\downarrow}x} + D_{\downarrow} e^{-ik_{\downarrow}x} \right\} \begin{pmatrix} -v^* \\ u \end{pmatrix} ,$$

where $u = \cos(\theta/2)$ and $v = \sin(\theta/2) \exp(i\phi)$. The \mathcal{S} -matrix relates the *flux amplitudes* of the in-states and out-states:

$$\begin{pmatrix} b_{\uparrow} \\ b_{\downarrow} \\ c_{\uparrow} \\ c_{\downarrow} \end{pmatrix} = \overbrace{\begin{pmatrix} r_{11} & r_{12} & t'_{11} & t'_{12} \\ r_{21} & r_{22} & t'_{21} & t'_{22} \\ t_{11} & t_{12} & r'_{11} & r'_{12} \\ t_{21} & t_{22} & r'_{21} & r'_{22} \end{pmatrix}}^{\mathcal{S}} \begin{pmatrix} a_{\uparrow} \\ a_{\downarrow} \\ d_{\uparrow} \\ d_{\downarrow} \end{pmatrix} .$$

Derive the 2×2 transmission matrix t (you don’t have to derive the entire \mathcal{S} -matrix) and thereby obtain the dimensionless conductance $g = \text{Tr}(t^\dagger t)$. Define the polarization P by

$$P = \frac{n_{\uparrow} - n_{\downarrow}}{n_{\uparrow} + n_{\downarrow}} ,$$

where $n_{\sigma} = k_{\sigma}/\pi$ is the electronic density. Find $g(P, \theta)$.

¹Note that it is the bare electron mass m_e which appears in the formula for μ_B and *not* the effective mass m^* !).

²For weakly magnetized systems, the magnetization is $\mathbf{M} = \mu_B^2 g(\varepsilon_F) \mathbf{H}_{\text{int}}$, where $g(\varepsilon_F)$ is the total density of states per unit volume at the Fermi energy.

[4] *Distribution of Resistances of a One-Dimensional Wire* – In this problem you are asked to derive an equation governing the probability distribution $P(\mathcal{R}, L)$ for the dimensionless resistance \mathcal{R} of a one-dimensional wire of length L . The equation is called the Fokker-Planck equation. Here’s a brief primer on how to derive Fokker-Planck equations.

Suppose $x(t)$ is a stochastic variable. We define the quantity

$$\delta x(t) \equiv x(t + \delta t) - x(t) , \quad (1)$$

and we assume

$$\begin{aligned} \langle \delta x(t) \rangle &= F_1(x(t)) \delta t \\ \langle [\delta x(t)]^2 \rangle &= 2 F_2(x(t)) \delta t \end{aligned}$$

but $\langle [\delta x(t)]^n \rangle = \mathcal{O}((\delta t)^2)$ for $n > 2$. The $n = 1$ term is due to *drift* and the $n = 2$ term is due to *diffusion*. Now consider the conditional probability density, $P(x, t | x_0, t_0)$, defined to be the probability distribution for $x \equiv x(t)$ given that $x(t_0) = x_0$. The conditional probability density satisfies the composition rule,

$$P(x, t | x_0, t_0) = \int_{-\infty}^{\infty} dx' P(x, t | x', t') P(x', t' | x_0, t_0) ,$$

for any value of t' . Therefore, we must have

$$P(x, t + \delta t | x_0, t_0) = \int_{-\infty}^{\infty} dx' P(x, t + \delta t | x', t) P(x', t | x_0, t_0) .$$

Now we may write

$$\begin{aligned} P(x, t + \delta t | x', t) &= \langle \delta(x - x' - \delta x(t)) \rangle \\ &= \left\{ 1 + \langle \delta x(t) \rangle \frac{d}{dx'} + \frac{1}{2} \langle [\delta x(t)]^2 \rangle \frac{d^2}{dx'^2} + \dots \right\} \delta(x - x') , \end{aligned}$$

where the average is over the random variables. Upon integrating by parts and expanding to $\mathcal{O}(\delta t)$, we obtain the Fokker-Planck equation,

$$\frac{\partial P}{\partial t} = -\frac{\partial}{\partial x} [F_1(x) P(x, t)] + \frac{\partial^2}{\partial x^2} [F_2(x) P(x, t)] .$$

That wasn’t so bad, now was it?

For our application, $x(t)$ is replaced by $\mathcal{R}(L)$. We derived the composition rule for series quantum resistors in class:

$$\begin{aligned} \mathcal{R}(L + \delta L) &= \mathcal{R}(L) + \mathcal{R}(\delta L) + 2 \mathcal{R}(L) \mathcal{R}(\delta L) \\ &\quad - 2 \cos \beta \sqrt{\mathcal{R}(L) [1 + \mathcal{R}(L)] \mathcal{R}(\delta L) [1 + \mathcal{R}(\delta L)]} , \end{aligned}$$

where β is a random phase. For small values of δL , we needn't worry about quantum interference and we can use our Boltzmann equation result. Show that

$$\mathcal{R}(\delta L) = \frac{e^2}{h} \frac{m^*}{n e^2 \tau} \delta L = \frac{\delta L}{2\ell},$$

where $\ell = v_F \tau$ is the elastic mean free path. (Assume a single spin species throughout.)

Find the drift and diffusion functions $F_1(\mathcal{R})$ and $F_2(\mathcal{R})$. Show that the distribution function $P(\mathcal{R}, L)$ obeys the equation

$$\frac{\partial P}{\partial L} = \frac{1}{2\ell} \frac{\partial}{\partial \mathcal{R}} \left\{ \mathcal{R} (1 + \mathcal{R}) \frac{\partial P}{\partial \mathcal{R}} \right\}.$$

Show that this equation may be solved in the limits $\mathcal{R} \ll 1$ and $\mathcal{R} \gg 1$, with

$$P(\mathcal{R}, z) = \frac{1}{z} e^{-\mathcal{R}/z}$$

for $\mathcal{R} \ll 1$, and

$$P(\mathcal{R}, z) = (4\pi z)^{-1/2} \frac{1}{\mathcal{R}} e^{-(\ln \mathcal{R} - z)^2/4z}$$

for $\mathcal{R} \gg 1$, where $z = L/2\ell$ is the dimensionless length of the wire. Compute $\langle \mathcal{R} \rangle$ in the former case, and $\langle \ln \mathcal{R} \rangle$ in the latter case.